

In the Claims:

Please amend claim 1, as follows:

1. (Twice Amended) A semiconductor device comprising:

a substrate coated with an insulating layer;

a connecting part connected to a conductive layer through the insulating layer of the substrate, the connecting part having an upper surface;

a seed separating layer formed around the connecting part and the insulating layer, the seed separating layer defining an open region that exposes at least part of the connecting part, the seed separating layer having an upper surface disposed above the upper surface of the connecting part;

a seed layer disposed in the open region of the seed separating layer and covering a first portion of the seed separating layer, the seed layer having an upper surface disposed above the upper surface of the seed separating layer and a lower surface that engages connecting part and that is disposed below the upper surface of the seed separating layer; and

a capacitor comprising a lower electrode formed on the seed layer, a dielectric medium formed on the lower electrode and further covering a second portion of the seed separating layer, and an upper electrode formed on the dielectric medium.

**REMARKS**

This paper is filed in response to the final office action mailed on December 11, 2002. Claim 1 has been amended; claims 1-12 are pending.

The office action rejects the claims under 35 U.S.C. § 102(b) as being anticipated by U.S. Patent No. 6,451,666 ("Hong") or obvious in view of the combination of Hong and U.S. Patent No. 6,458,689 ("Yu") or Hong in combination with U.S. Patent No. 6,420,267 ("Lin"). In response, claim 1 has been amended to distinguish Hong thereby traversing both the anticipation and obviousness rejections.

Specifically, claim 1 recites a structure whereby the seed layer 46 has an upper surface disposed above the upper surface of the seed separating layer 45 and the seed layer 46 further has a lower surface that engages the connecting part 44 and that is further disposed below the upper surface of the seed separating layer 45. This structure is clearly illustrated in Figs. 3B-3D and Fig. 4.